



FZT651Q

60V NPN MEDIUM POWER TRANSISTOR IN SOT223

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

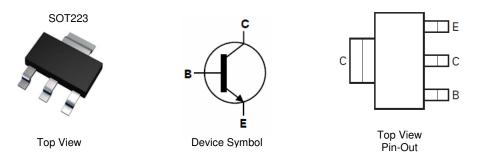
Features

- BV_{CEO} > 60V
- I_C = 3A High Continuous Current
- I_{CM} = 6A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 300mV @1A
- Complementary PNP Type: DIODES™ FZT751Q
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES[™] FZT651Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified. PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic. "Green" Molding Compound;
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208⁽³⁾
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

Dout Number	Deekene	Maulsina	Deal Cine (in also)		Pac	cking
Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Qty.	Carrier
FZT651QTA	SOT223 (Type DN)	FZT651	7	12	1,000	Reel
FZT651QTC	SOT223 (Type DN)	FZT651	13	12	4,000	Reel

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

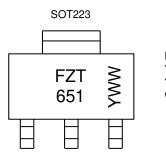
Lead-free

Notes:

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



FZT 651 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2 = 2022) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	3	A
Peak Pulse Current	Ісм	6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D	2	W
Power Dissipation	(Note 6)	P _D	3	W
The word Desistence, hunstice to Ambient	(Note 5)		62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R _{eja}	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)		R _{θJL}	12.9	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

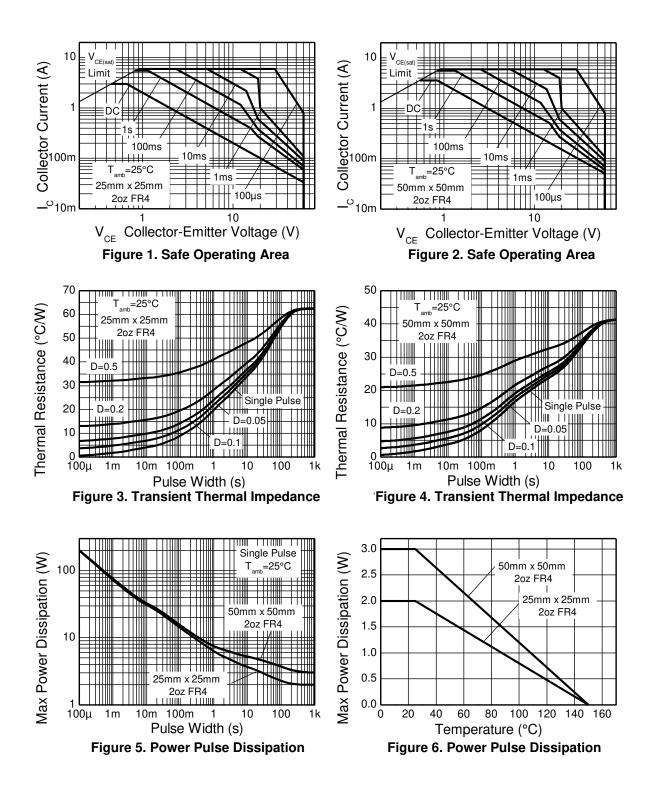
Notes: 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

6. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.

Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

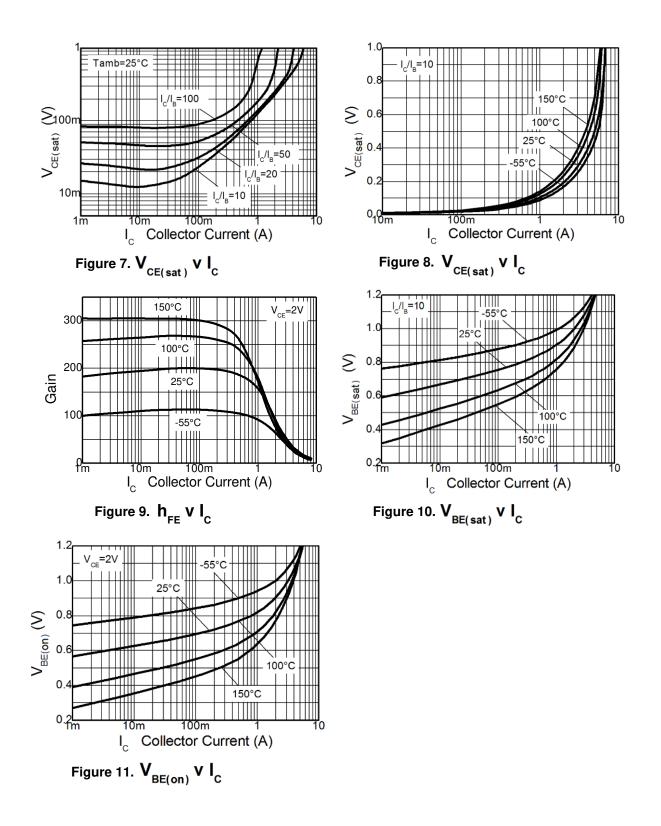
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector Out off Ourrent	I _{СВО}	_	—	0.1		$V_{CB} = 60V$
Collector Cut-off Current		_	—	10	μA	$V_{CB} = 60V, T_A = +125^{\circ}C$
Emitter Cut-off Current	I _{EBO}	_	—	100	nA	$V_{EB} = 4V$
Collector Emitter Seturation Voltage (Note 0)	V _{CE(sat)}	_	0.12	0.3	V	$I_{C} = 1A, I_{B} = 100mA$
Collector-Emitter Saturation Voltage (Note 9)		_	0.35	0.6		$I_{C} = 3A, I_{B} = 300mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	0.9	1.25	V	$I_{C} = 1A, I_{B} = 100mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	0.8	1.0	V	$I_C = 1A, V_{CE} = 2V$
	hfe	70	200	—		$I_{C} = 50 mA, V_{CE} = 2V$
		100	200	300		$I_{C} = 500 \text{mA}, V_{CE} = 2 \text{V}$
DC Current Gain (Note 9)		80	170	—		$I_C = 1A, V_{CE} = 2V$
		40	80	—		$I_C = 2A, V_{CE} = 2V$
Current Gain-Bandwidth Product (Note 9)	f⊤	140	175	_	MHz	$V_{CE} = 5V$, $I_C = 100mA$, f = 100MHz
Quitable Times	t _{on}		45	_		$I_{C} = 500 \text{mA}, V_{CC} = 10 \text{V},$
Switching Times	t _{off}		800	_	ns	$I_{B1} = -I_{B2} = 50mA$
Output Capacitance (Note 9)	Cobo	_	_	30	pF	V _{CB} = 10V, f = 1MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



FZT651Q

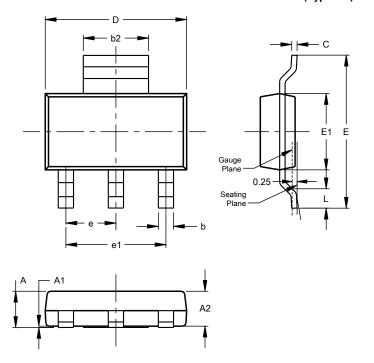
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

Please see https://www.diodes.com/design/support/packaging/ for the latest version.

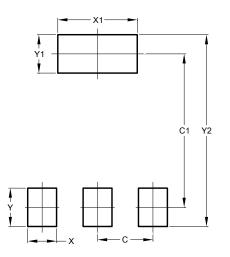


SOT223 (Type DN)						
Dim	Min	Max	Тур			
Α		1.70				
A1	0.01	0.15				
A2	1.50	1.68	1.60			
b	0.60	0.80	0.70			
b2	2.90	3.10				
c	0.20	0.32				
D	6.30	6.70				
ш	6.70	7.30				
E1	3.30	3.70				
e			2.30			
e1			4.60			
L	0.85					
All Dimensions in mm						

Suggested Pad Layout

Please see https://www.diodes.com/design/support/packaging/ for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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